A Facile Strategy for Fabricating the Hierarchical Nanocomposites of V_2O_5 Nanowire Arrays on Three-Dimension N-doped Graphene aerogel with Synergistic Effect for Supercapacitor[†]

Wei Sun, ^a Guohua Gao, ^{a,*} Yuchuan Du, ^{b,*}Kun Zhang, ^a and Guangming Wu,^{a,*}

^aShanghai Key Laboratory of Special Artificial Microstructure Materials and Technology, School of Physics and Science Engineering, Tongji University, Shanghai, 200092, PR China. Email: <u>gao@tongji.edu.cn; wugm@tongji.edu.cn</u>.

^bKey Laboratory of Road and Traffic Engineering (Ministry of Education), Tongji University, Shanghai, 200092, PR China. Email: <u>ycdu@tongji.edu.cn</u>.

Computational methods. Density functional theory (DFT) analysis was applied to investigate the crystal structures of graphene, N-doped graphene and the growth of VO_x on it. All the calculations in this paper were performed by using the Vienna ab initio simulation package (VASP),¹ the exchange and correlation energy functional was treated by the Perdew-Burke-Ernzerh of variant of the generalized gradient approximation (GGA).² Interaction between ion and electrons were described with projector augmented wave pseudo potentials (PAW) approach,^{3,4} and the energy cutoff for the plane wave basis set was set to be 400 eV. All calculations were considered in the spin-unrestricted manner, but no magnetic moments were detected. The first Brillouin zone was sampled using a $5 \times 5 \times 1$ Γ -centered k-point grid. The vacuum slab was set to be 15 Å.

EXPERIMENTAL

Synthesis of N-GA. All the chemicals are obtained as chemically pure grade products and used without any further treatment. Graphene oxide (GO) was prepared from commercially available graphite flakes according to the modified Hummers method in our previous paper. N-doped graphene aerogel (N-GA) was synthesized by following the procedure reported elsewhere with slight modifications. In a typical procedure, 0.5 mL pyrrole monomer was suspended in 10 mL GO aqueous dispersion (3 mg L⁻¹) and thoroughly dispersed with ultrasonic treatment for 15 min. Then, the pH was adjusted in the range 11.1-11.3 with moderate ethylenediamine under vigorous stirring at room temperature. After 10 min, the resulting suspension was sealed in a glass vial and heated for 8 h at 90 °C for preparation of hydrogel. Finally, N-GA was obtained after heating the pre-freeze-dried graphen gel at 900 °C for 3 h under Ar atmosphere.

Preparation of the N-GA@V₂O₅ NWAs. The prepared N-GA was used as the backbone for the growth of V₂O₅ NWAs by a facile hydrothermal synthesis method. 0.3 g commercial V₂O₅ powder and H₂C₂O₄•2H₂O in a molar ratio of 1:3 was dissolved in 15 mL of deionized H₂O under vigorous stirring at 65 °C for 1 h until a clear dark blue solution was formed. Then 2.5 mL of 30 % H₂O₂ was added and kept continuously stirring for about 20 min, followed by addition of 60 mL ethanol. After putting N-CA cylinder (Φ 2cm × 2 cm), the solution was then transferred into a Teflon-lined stainless autoclave. The autoclave was sealed and maintained at 160 °C for 2 h. After the autoclave cooled down to room temperature, the product was washed, freeze dried and then thermal treated at 300 °C for 2 h to obtain the N-GA@V₂O₅ NWAs. **Characterization.** The as-prepared samples were characterized by SEM (XL30FEG), TEM (JEOL-2100 TEM operating at 200 kV), FTIR spectroscopy (Bruker-TEMSOR27), and rotation anode X-ray powder diffraction (XRD) (Rigaku D/max-C) equipped with Cu K α radiation source ($\lambda = 1.5406$ Å). Raman spectra (Jobin-Yvon HR800) were recorded by using a 514 nm argon ion laser (source power 17 mW). X-Ray photoelectron spectroscopy (XPS) was performed using a PHI 5300 spectrometer (Perkin-Elmer) operated at 14 kV. N₂ sorption measurements were operated with Autosorb-1 (Quantchome, USA) at 77 K using Barrett-Emmett-Teller (BET) calculations for the surface area. The pore size distribution plot was recorded from the adsorption branch of the isotherm based on the Barrett-Joyner-Halenda (BJH) model. The thermogravimetry analysis (TGA) and different thermogravimetry analysis (DTG) were carried out on a SDT Q600 over the temperature range from 50 to 900 °C using a heating rate of 10 °C min⁻¹ under air atmosphere.

Electrochemical performance measurements. Electrochemical measurements were carried out using three-electrode systems by using a 8 M LiCI aqueous solution as electrolyte. The mixture containing 85 wt% active material, 10 wt% conducting acetylene black, and 5 wt% poly(vinylidene flouride) (PVDF) was well mixed by using N-methlpyrrolidone (NMP) as the solvent. The as-prepared mixed slurry (about 1 mg) was coated onto graphite paper with area of 1 cm² and then the electrode was dried at 120 °C for 12 h under vacuum to remove the solvent. Cyclic voltammetry (CV) and galvanostatic charge/discharge curves were measured by a CHI 660D electrochemical workstation with the potential being swept from -0.3 to +0.7 V. For electrochemical

impedance spectroscopy (EIS), the amplitude of the sine perturbation signal was 5 mV, and the frequency was scanned from the highest (100 kHz) to the lowest (10 mHz). The specific capacitance was calculated according to the equation as $C = I\Delta t/m\Delta V$, where I is the discharge current (A), Δt is the discharge time, m is the total mass of active material, and ΔV is the discharge voltage. The energy and powder densities were estimated by using the formula $E = C(\Delta V)^2/2$ and $P = Q\Delta V/2t = E/\Delta t$.



Figure S1. XPS spectrum of the 3D Ppy@GO aerogel and 3D N-GA.



Figure S2. TG-DSC curves of N-GA@VO_x NWAs under an air atmosphere.

TG-DSC measurements were carried out to investigate the whole sintering process. As shown in DSC curve, three exothermic peaks appeared at 220 °C and 463 °C, which are derived from the oxidation of low valence V⁴⁺ to high valence V⁵⁺ and the decomposition of N-GA in air, respectively. The endothermic peak at 664 °C is caused by the liquefaction of crystal V₂O₅. According the analysis of the TG-DSC curves, 300 °C is enough for the oxidation V⁴⁺, which is corresponding the experimental results that greenish black N-GA@VO_x NWAs change into yellow N-GA@V₂O₅ NWAs after thermal treatment at 300 °C in air.



Figure S3. (a,b) SEM images of the N-GA@VO_x NWAs; inset: the photograph (a) of the corresponding sample.



Figure S4. (a) Nitrogen sorption isotherms and (b) corresponding pore size distribution of 3D

N-GA@V₂O₅ NWAs.



Figure S5. The corresponding EDS results of the N-GA@VO_x NWAs samples fabricated at different reaction intervals: (a) 30 min, (b) 45 min, and (c) 60 min.



Figure S6. Structures of the possible 7 isomers for 2 nitrogen atoms doping into graphene lattice.

Isomers	а	b	c	d	e	f	g
G _{fe} (eV)	-	-264.42	-263.44	-264.50	-264.73	-	-
	263.27					262.92	262.37

Table S1. The corresponding free energy (G_{fe}) of possible isomers in Figure S5.



Figure S7. Structures of 1, 2, 4, and 10 VO_2 molecules growing on the N-doped graphene (isomer-5).

Configurations	а	b	с	d	e
ΔE (eV)	-3.59	-4.04	-3.87	-4.03	-4.40

Table S2. The corresponding ΔE of configurations in Figure S7.



Figure S8. (a,b) SEM images of $GA@VO_x$ without N doping treatment fabricated at different reaction intervals: (a) 30 min, (b) 60 min, (c) 90 min, and (d) 120 min.



Figure S9. (a, c and e) CV curves of the N-GA, $GA@V_2O_5$ and N-GA $@V_2O_5$ NWAs at different sweep rates; (b, d and f) Galvanostatic charge-discharge curves of the N-GA, $GA@V_2O_5$ and N-GA $@V_2O_5$ NWAs at the different current density.



Figure S10. (a) CV curves of the N-GA@V₂O₅ NWAs with different reaction times at the sweep rate of 5 mV s⁻¹; (b) Galvanostatic charge-discharge curves of N-GA@V₂O₅ NWAs with different reaction times at the current density of 0.5 A g⁻¹; (c) influence of reaction times on the specific capacitance of N-GA@V₂O₅ NWAs; (d) specific capacitance of the N-GA@V₂O₅ NWAs with different reaction times as a function of current density.



Figure S11. Cycling performance at a constant current density of 10 A g⁻¹.



Figure S12. (a,b) SEM images of 3D N-GA@ V_2O_5 NWAs after cycling for 20000 cycles.

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